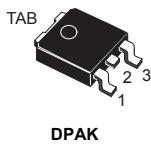
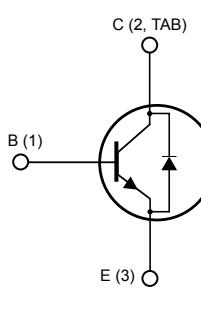


High voltage fast-switching NPN power transistor

Features



- High voltage capability
- Integrated free-wheeling diode
- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed
- Fully characterized at 125 °C
- Large RBSOA



NPNB1C2EE_D

Applications

- Electronic ballast for fluorescent lighting
- Switch mode power supplies

Description

This device is a high voltage fast-switching NPN power transistor, manufactured using high voltage multi-epitaxial planar technology for high switching speeds. It employs a cellular emitter structure with planar edge termination to enhance switching speeds, while maintaining a wide RBSOA.



Product status link

[STB13007DT4](#)

Product summary

Order code	STB13007DT4
Marking	B13007D
Package	D²PAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum rating

Symbol	Parameter	Value	Unit
V_{EBO}	Emitter-base voltage ($I_C = 0 \text{ A}$)	9	V
V_{CEV}	Collector-emitter voltage ($V_{BE} = -1.5 \text{ V}$)	700	V
V_{CEO}	Collector-emitter voltage ($I_B = 0 \text{ A}$)	400	V
I_C	Collector current	8	A
I_{CM}	Collector peak current ($t_P < 5 \text{ ms}$)	16	A
I_B	Base current	4	A
I_{BM}	Base peak current ($t_P < 5 \text{ ms}$)	8	A
P_{TOT}	Total power dissipation at $T_C = 25 \text{ }^\circ\text{C}$	80	W
T_{stg}	Storage temperature range	-65 to 150	$^\circ\text{C}$
T_J	Maximum operating junction temperature	150	$^\circ\text{C}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	1.56	$^\circ\text{C}/\text{W}$
R_{thJA}	Thermal resistance, junction-to-ambient	62.5	$^\circ\text{C}/\text{W}$

2 Electrical characteristics

$T_C = 25^\circ\text{C}$ unless otherwise specified.

Table 3. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector cut-off current	$V_{CE} = 700 \text{ V}, V_{BE} = 0 \text{ V}$	-	-	0.01	mA
		$V_{CE} = 700 \text{ V}, V_{BE} = 0 \text{ V}, T_J = 100^\circ\text{C}$ ⁽¹⁾	-	-	0.5	
I_{CEO}	Collector cut-off current	$V_{CE} = 400 \text{ V}, I_B = 0 \text{ A}$	-	-	100	µA
I_{EBO}	Emitter cut-off current	$V_{EB} = 9 \text{ V}, I_C = 0 \text{ A}$	-	-	100	µA
$V_{CEO(\text{sus})}$ ⁽²⁾	Collector-emitter sustaining voltage	$I_C = 10 \text{ mA}, I_B = 0 \text{ A}$	400	-	-	V
$V_{CE(\text{sat})}$ ⁽²⁾	Collector-emitter saturation voltage	$I_C = 2 \text{ A}, I_B = 0.4 \text{ A}$	-	-	0.8	V
		$I_C = 5 \text{ A}, I_B = 1 \text{ A}$	-	-	1.5	
		$I_C = 5 \text{ A}, I_B = 1 \text{ A}, T_J = 100^\circ\text{C}$ ⁽¹⁾	-	-	3	
		$I_C = 8 \text{ A}, I_B = 2 \text{ A}$	-	-	2	
$V_{BE(\text{sat})}$ ⁽²⁾	Base-emitter saturation voltage	$I_C = 2 \text{ A}, I_B = 0.4 \text{ A}$	-	-	1.2	V
		$I_C = 5 \text{ A}, I_B = 1 \text{ A}$	-	-	1.6	
		$I_C = 5 \text{ A}, I_B = 1 \text{ A}, T_J = 100^\circ\text{C}$ ⁽¹⁾	-	-	1.5	
h_{FE}	DC current gain	$I_C = 2 \text{ A}, V_{CE} = 5 \text{ V}$	18	-	40	
		$I_C = 5 \text{ A}, V_{CE} = 5 \text{ V}$	8	-	25	
V_f	Diode forward voltage	$I_C = 3 \text{ A}$	-	-	2.5	V
	Inductive load	$V_{\text{Clamp}} = 250 \text{ V}, I_C = 5 \text{ A}$	-	-	-	
t_s	Storage time	$V_{BE(\text{off})} = -5 \text{ V}, I_{B1} = 1 \text{ A}$	-	1.7	2.3	µs
t_f	Fall time	$R_{BB} = 0 \Omega, L = 200 \mu\text{H}$ (see the Figure 10. Inductive load switching test circuit)	-	90	150	ns
	Inductive load	$V_{\text{Clamp}} = 250 \text{ V}, I_C = 5 \text{ A}$	-	-	-	
t_s	Storage time	$V_{BE(\text{off})} = -5 \text{ V}, I_{B1} = 1 \text{ A}$	-	2.2	-	µs
t_f	Fall time	$R_{BB} = 0 \Omega, L = 200 \mu\text{H}, T_J = 125^\circ\text{C}$ (see the Figure 10. Inductive load switching test circuit)	-	150	-	ns

1. Specified by design, not tested in production.

2. Pulsed: Pulse duration = 300 µs, duty cycle ≤ 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

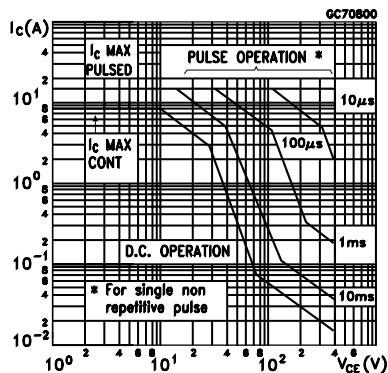


Figure 2. Derating curve

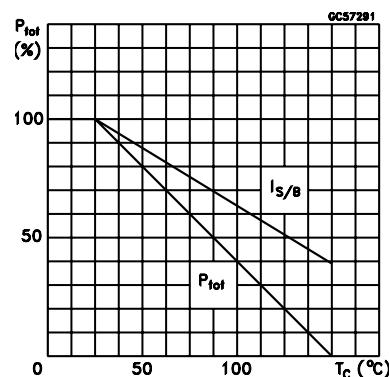


Figure 3. Diode forward voltage

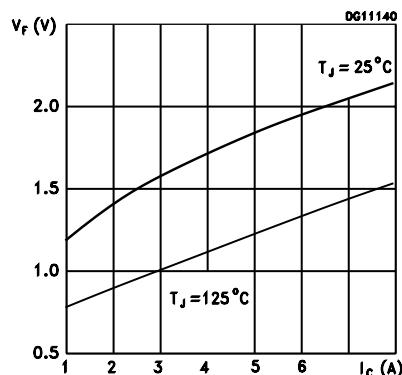


Figure 4. Reverse biased safe operating area

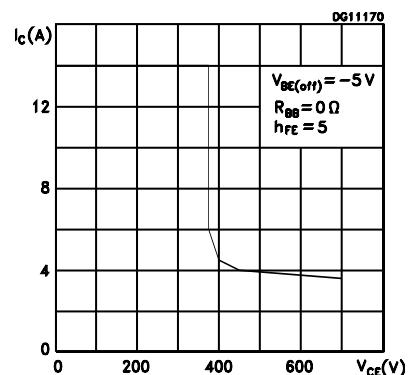


Figure 5. DC current gain ($V_{CE} = 1.5$ V)

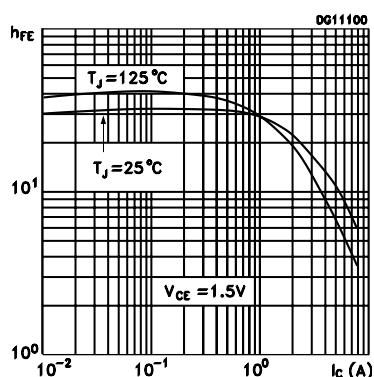


Figure 6. DC current gain ($V_{CE} = 5$ V)

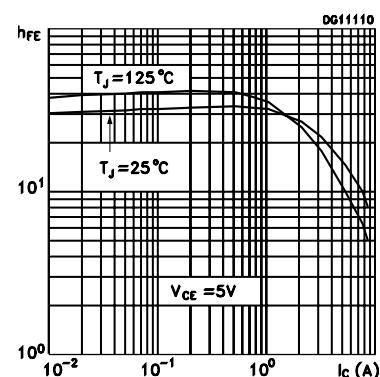
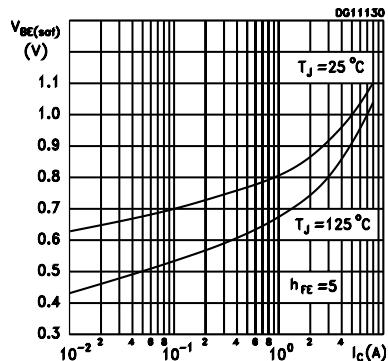
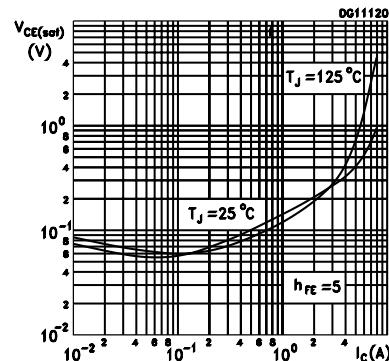
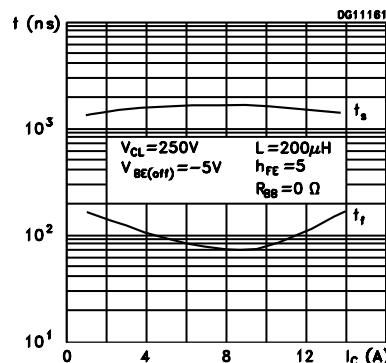
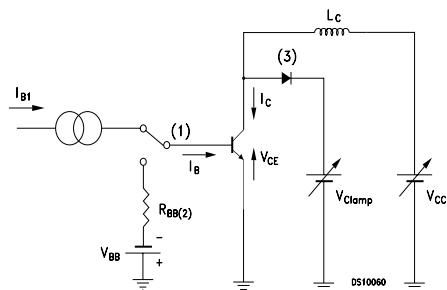


Figure 7. Base-emitter saturation voltage

Figure 8. Collector-emitter saturation voltage

Figure 9. Inductive load switching times


3 Test circuits

Figure 10. Inductive load switching test circuit



Note:

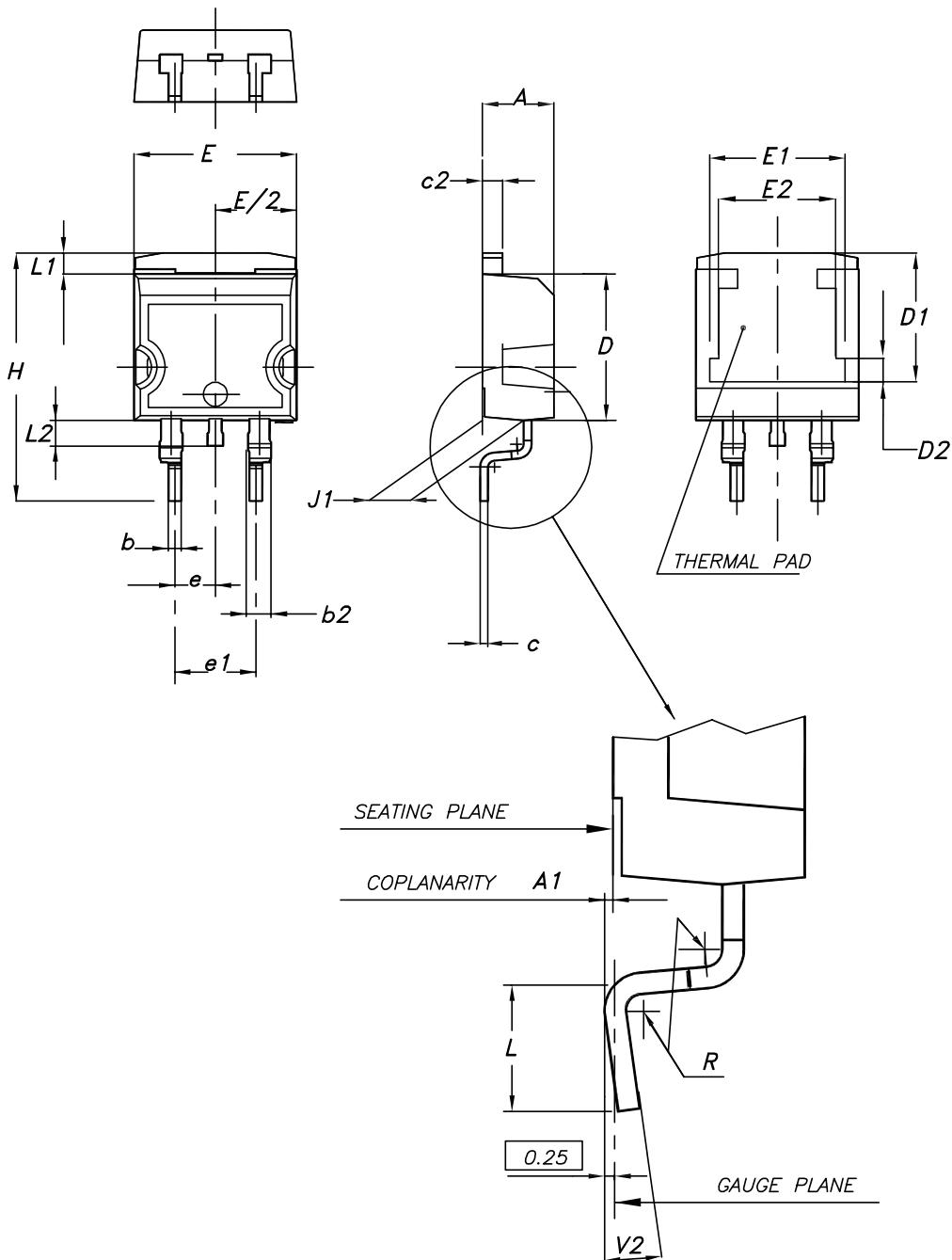
- (1) Fast electronic switch
- (2) Non-inductive resistor
- (3) Fast recovery rectifier

4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 D²PAK (TO-263) type A package information

Figure 11. D²PAK (TO-263) type A package outline

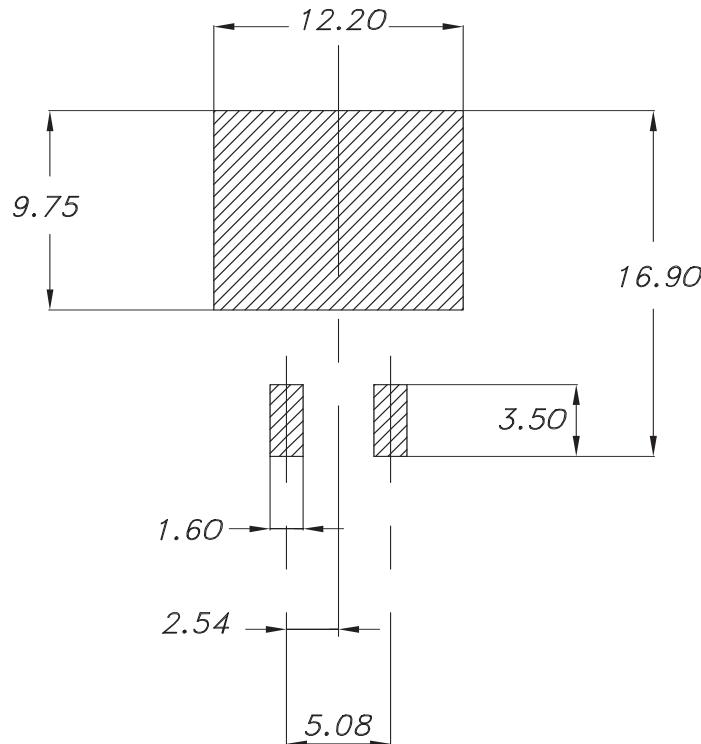


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Table 4. D²PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.30	8.50	8.70
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

Figure 12. D²PAK (TO-263) recommended footprint (dimensions are in mm)

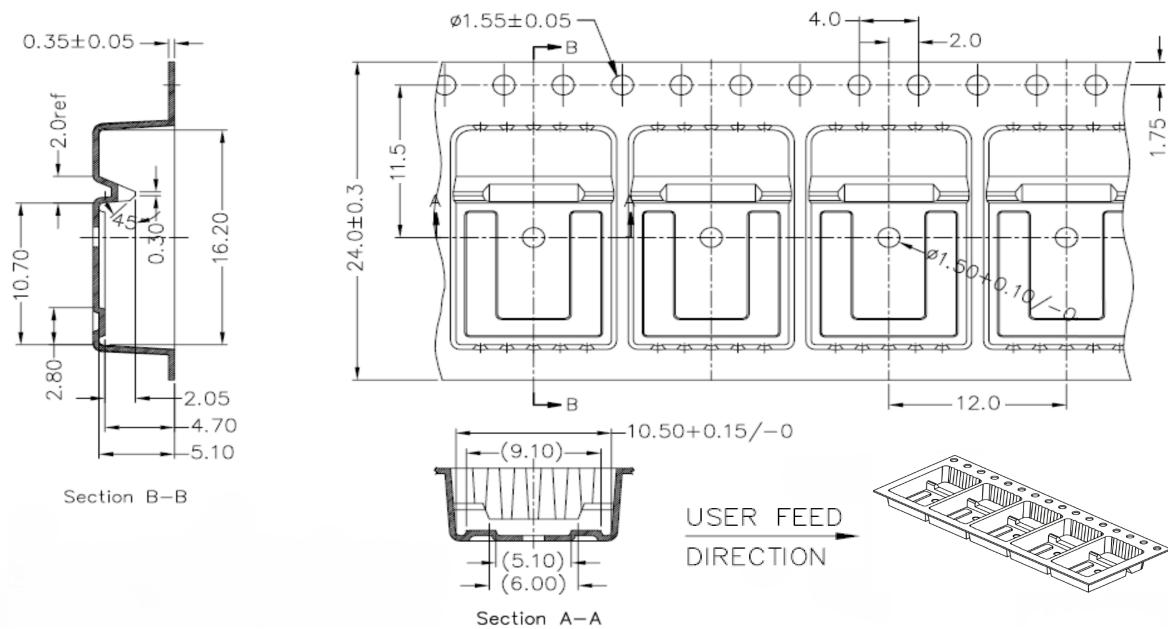


0079457_Rev27_footprint

4.2

D²PAK packing information

Figure 13. D²PAK tape drawing (dimensions are in mm)



0079900_14

Revision history

Table 5. Document revision history

Date	Revision	Changes
19-Jun-2006	1	Initial release.
27-Apr-2007	2	The package's mechanical data has been update on page 7.
11-Jun-2025	3	Updated Section 4: Package information . Minor text changes.

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